

Session 15

15. Oxide TFT III

Wednesday, October 12, 2011 / 15:10 ~ 16:35

Room 303

Chairs: Jin-Seong Park (Dankook Univ., Korea)

Junichi Koike (Tohoku Univ., Japan)

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| 15:10 ~ 15:35 | 15-1 | [Invited] Density of Trap States of Measured by Photo-Excited Charge-Collection Spectroscopy into Oxide Thin-film Transistors
<i>Seongil Im, Youn-Gyoung Chang (Yonsei Univ., Korea), Tae Woong Moon (LG Display Co., Ltd., Korea), Kimoon Lee (Tokyo Inst. of Tech., Japan), and Jae Hoon Kim (Yonsei Univ., Korea)</i> |
| 15:35 ~ 15:55 | 15-2 | Drain Bias Induced Instability Characteristics in Oxide Thin Film Transistors
<i>Shinhyuk Yang, Jun Yong Bak (ETRI, Korea), Sung-Min Yoon (Kyung Hee Univ., Korea), Min Ki Ryu, Himchan Oh, Chi-Sun Hwang, Sang-Hee Ko Park (ETRI, Korea), and Jin Jang (Kyung Hee Univ., Korea)</i> |
| 15:55 ~ 16:15 | 15-3 | Electrode Bottom Titanium Oxide Induced Amorphous Indium–Gallium–Zinc Oxide Thin-Film Transistors Instability
<i>Lung-Pao Hsin, Tsung-Hsiang Shih, Shou-Wei Fang, Guan-Yu Lin, Jen-Yu Lee, Yu-Hung Chen, Hsin-Hung Li, Chin-Wei Yang, Chien-Tao Chen, Hsiung-Hsing Lu, Kai-Chung Cheng, Chih-Yuan Lin, Chia-Yu Chen, Chun-Ming Yang, He-Ting Tsai, and Yu-Hsin Lin (AU Optronic</i> |
| 16:15 ~ 16:35 | 15-4 | Zirconium-Zinc-Tin Oxide Thin-Film Transistors Using a Solution Process
<i>You Seung Rim, Dong Lim Kim, Woong Hee Jeong, Hyun Soo Lim, and Hyun Jae Kim (Yonsei Univ., Korea)</i> |